AVF250

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AVF250** is Designed for
Class C, IFF Applications up to 1090 MHz.

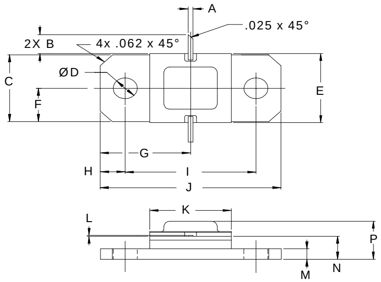
FEATURES:

- Internal Input/Output Matching Networks
- **P_G** = 8.5 dB at 250 W/1090 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	18.8 A
V_{CC}	55 V
P_{DISS}	625 W @ T_C = 25 °C
T_J	-65 °C to +2500 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	0.6 °C/W

PACKAGE STYLE .400 2NL FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.020 / 0.51	.030 / 0.76
B	.100 / 2.54	
C	.376 / 9.55	.396 / 10.06
D	.110 / 2.79	.130 / 3.30
E	.395 / 10.03	.407 / 10.34
F	.193 / 4.90	
G	.450 / 11.43	
H	.125 / 3.18	
I	.640 / 16.26	.660 / 16.76
J	.890 / 22.61	.910 / 23.11
K	.395 / 10.03	.415 / 10.54
L	.004 / 0.10	.007 / 0.18
M	.052 / 1.32	.072 / 1.83
N	.118 / 3.00	.131 / 3.33
P		.230 / 5.84

ORDER CODE: ASI10571

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 10 Ma	65			V
BV_{CER}	I_C = 25 mA R_{BE} = 10 Ω	65			V
BV_{EBO}	I_E = 1.0 mA	3.5			V
I_{CES}	V_{CE} = 50 V			25	mA
h_{FE}	V_{CE} = 5.0 V I_C = 1.0 A	15		120	---
P_G η_C	V_{CC} = 50 V P_{OUT} = 250 W f = 1030 - 1090 MHz	8.5 35			dB %